

AMENDMENTS TO THE SPECIFICATION

Please amend paragraph **[0001]** starting at page 1, line 4, as follows:

[0001] This application claims the benefit of Korean Patent Application No. 1999-50512, filed on November 15, 1999, under 35 U.S.C. § 119, and U.S. Application No. 09/712,190, the parent Application to this Divisional Application (which issued as U.S. Patent 6,717,638 on April 6, 2004), and the entirety of these Applications are hereby incorporated by reference.

Please amend paragraph **[0016]** starting at page 4, line 15 as follows:

[0016] The thin film transistor further includes: a gate insulating layer on the substrate and covering the gate electrode; and a semiconductor layer formed on the gate insulating layer, having an amorphous silicon layer and a doped amorphous silicon layer, wherein the gate electrode is formed on the substrate and the source and drain electrode are spaced apart ~~from~~ from each other and overlap both end portions of the doped amorphous silicon layer, respectively.